

OGEN FRA

FADER

RoHS Compliance

CAT25C33/65

32K/64K-Bit SPI Serial CMOS EEPROM

FEATURES

- 10 MHz SPI compatible
- 1.8 to 6.0 volt operation
- Hardware and software protection
- Low power CMOS technology
- SPI modes (0,0 &1,1)
- Commercial, industrial, automotive and extended temperature ranges
- 1,000,000 program/erase cycles
- 100 year data tetention
- Self-timed write cycle
- 8-pin DIP/SOIC and 14-pin TSSOP
- 64-byte page write buffer
- Block write protection Protect first page, last page, any 1/4 or lower 1/2 of EEPROM array

DESCRIPTION

The CAT25C33/65 is a 32K/64K-Bit SPI Serial CMOS EEPROM internally organized as 4Kx8/8Kx8 bits. Catalyst's advanced CMOS Technology substantially reduces device power requirements. The CAT25C33/ 65 features a 64-byte page write buffer. The device operates via the SPI bus serial interface and is enabled though a Chip Select (\overline{CS}). In addition to the Chip Select, the clock input (SCK), data in (SI) and data out (SO) are required to access the device. The HOLD pin may be used to suspend any serial communication without resetting the serial sequence. The CAT25C32/64 is designed with software and hardware write protection features including Block write protection. The device is available in 8-pin DIP, 8-pin SOIC, 14-pin TSSOP and 20-pin TSSOP packages.

PIN CONFIGURATION

SOIC Package (S, V, GV) TSSOP Package (U14, Y14)

CS [] SO [] VSS [] VSS []	•1 2 3 4	8	CS □ 1 14 SO □ 2 13 NC □ 3 12 NC □ 4 11 NC □ 5 10 WP □ 6 9	VCC HOLD NC NC NC NC NC SCK
DIP Pac	kage	(P, L, GL)	V _{SS} □ <u>7 8</u>	SI

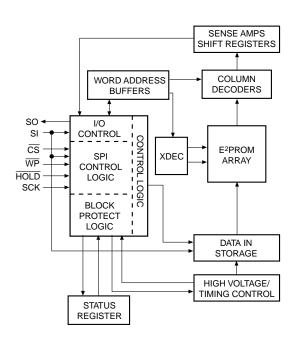
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cs 🗆	•1	• ₈		Vcc
SO 🗆	2	7	Þ	HOLD
WP 🗆	3	6	白	SCK
Vss □	4	5	Ь	SI

PIN FUNCTIONS

Pin Name	Function
SO	Serial Data Output
SCK	Serial Clock
WP	Write Protect
Vcc	+1.8V to +6.0V Power Supply
V _{SS}	Ground
CS	Chip Select
SI	Serial Data Input
HOLD	Suspends Serial Input
NC	No Connect

BLOCK DIAGRAM





ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias–55°C to +125°C
Storage Temperature65°C to +150°C
Voltage on any Pin with Respect to $V_{SS}{}^{1)}$ –2.0V to +V_{CC} +2.0V
V_{CC} with Respect to V_{SS}
Package Power Dissipation Capability (Ta = 25°C)1.0W
Lead Soldering Temperature (10 secs)
Output Short Circuit Current ⁽²⁾ 100 mA

*COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions outside of those listed in the operational sections of this specification is not implied. Exposure to any absolute maximum rating for extended periods may affect device performance and reliability.

RELIABILITY CHARACTERISTICS

Lead Solde					
Output Sho	rt Circuit Current ⁽²⁾	100 mA			
RELIABILIT	Y CHARACTERISTICS				
Symbol	Parameter	Min.	Тур.	Max.	Units
Nend ⁽³⁾	Endurance	1,000,000			Cycles/Byte
T _{DR} ⁽³⁾	Data Retention	100			Years
VZAP ⁽³⁾	ESD Susceptibility	2000			Volts
I _{LTH} ⁽³⁾⁽⁴⁾	Latch-up	100			mA

D.C. OPERATING CHARACTERISTICS

 V_{CC} = +1.8V to +6.0V, unless otherwise specified.

		Limits				
Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
I _{CC1}	Power Supply Current (Operating Write)			10	mA	V _{CC} = 5V @ 10MHz SO=open; CS=Vss
I _{CC2}	Power Supply Current (Operating Read)			2	mA	$V_{CC} = 5.0V$ $F_{CLK} = 10MHz$
I _{SB} ⁽⁵⁾ Power Supply Current (Standby)				1	μA	$\overline{CS} = V_{CC}$ $V_{IN} = V_{SS} \text{ or } V_{CC}$
ILI	Input Leakage Current			2	μΑ	
I _{LO}	Output Leakage Current			3	μA	$V_{OUT} = 0V$ to V_{CC} , CS = 0V
V _{IL} (3)	Input Low Voltage	-1		V _{CC} x 0.3	V	
V _{IH} ⁽³⁾	Input High Voltage	V _{CC} x 0.7		V _{CC} + 0.5	V	
VOL1	Output Low Voltage			0.4	V	4.5V≤V _{CC} <5.5V
V _{OH1}	Output High Voltage	V _{CC} - 0.8			V	I _{OL} = 3.0mA I _{OH} = -1.6mA
Vol2	Output Low Voltage			0.2	V	1.8V≤V _{CC} <2.7V
V _{OH2}	Output High Voltage	V _{CC} -0.2			V	I _{OL} = 150μΑ I _{OH} = -100μΑ

Note:

(1) The minimum DC input voltage is -0.5V. During transitions, inputs may undershoot to -2.0V for periods of less than 20 ns. Maximum DC voltage on output pins is V_{CC} +0.5V, which may overshoot to V_{CC} +2.0V for periods of less than 20 ns.

(2) Output shorted for no more than one second. No more than one output shorted at a time.

These parameter are tested initially and after a design or process change that affects the parameter according to appropriate AEC-Q100 (3) and JEDEC test methods.

(4) Latch-up protection is provided for stresses up to 100 mA on address and data pins from -1V to V_{CC} +1V.

(5) Maximum standby current (I_{SB}) = 10 μ A for the Automotive and Extended Automotive temperature range.



PIN CAPACITANCE (1)

Symbol	Test Conditions	Max.	Units	Conditions
COUT	Output Capacitance (SO)	8	pF	V _{OUT} =0V
CIN	Input Capacitance (CS, SCK, SI, WP, HOLD)	6	pF	V _{IN} =0V

Applicable over recommended operating range from $T_A=25$ °C, f=1.0 MHz, VCC= ± 5.0 V (unless otherwise noted).

A.C. CHARACTERISTICS

				Li	mits				
			= 6.0V	V _{CC} = 2.5V-6.0V		V _{CC} = 4.5V-5.5V			Test
SYMBOL	PARAMETER	Min.	Max.	Min.	Max.	Min.	Max.	UNITS	Conditions
ts∪	Data Setup Time	50		50		20		ns	
t _H	Data Hold Time	50		50		20		ns	
t _{WH}	SCK High Time	250		125		40		ns	
t _{WL}	SCK Low Time	250		125		40		ns	
fscк	Clock Frequency	DC	1	DC	3	DC	10	MHz	
t _{LZ}	HOLD to Output Low Z		50		50		50	ns	
t _{RI} ⁽¹⁾	Input Rise Time		2		2		2	μs	
t _{FI} ⁽¹⁾	Input Fall Time		2		2		2	μs	$C_L = 50 pF$
t _{HD}	HOLD Setup Time	100		100		40		ns	
t _{CD}	HOLD Hold Time	100		100		40		ns	
twc	Write Cycle Time		10		10		5	ms	
t _V	Output Valid from Clock Low		250		250		80	ns	
t _{HO}	Output Hold Time	0		0		0		ns	
t _{DIS}	Output Disable Time		250		250		75	ns	
t _{HZ}	HOLD to Output High Z		150		100		50	ns	
t _{CS}	CS High Time	500		250		200		ns	
tcss	CS Setup Time	500		250		100		ns	
tсsн	CS Hold Time	500		250		100		ns	

NOTE:

(1) This parameter is tested initially and after a design or process change that affects the parameter.



FUNCTIONAL DESCRIPTION

The CAT25C33/65 supports the SPI bus data transmission protocol. The synchronous Serial Peripheral Interface (SPI) helps the CAT25C33/65 to interface directly with many of today's popular microcontrollers. The CAT25C33/65 contains an 8-bit instruction register. (The instruction set and the operation codes are detailed in the instruction set table)

After the device is selected with \overline{CS} going low, the first byte will be received. The part is accessed via the SI pin, with data being clocked in on the rising edge of SCK. The first byte contains one of the six op-codes that define the operation to be performed.

Figure 1. Sychronous Data Timing

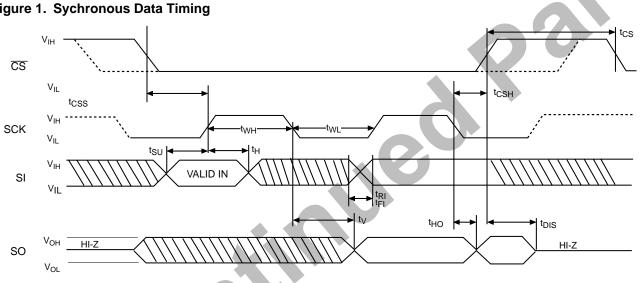
PIN DESCRIPTION

SI: Serial Input

SI is the serial data input pin. This pin is used to input all opcodes, byte addresses, and data to be written to the 25C33/65. Input data is latched on the rising edge of the serial clock.

SO: Serial Output

SO is the serial data output pin. This pin is used to transfer data out of the 25C33/65. During a read cycle, data is shifted out on the falling edge of the serial clock.



Note: Dashed Line= mode (1, 1)

INSTRUCTION SET

Instruction	Opcode	Operation
WREN	0000 0110	Enable Write Operations
WRDI	0000 0100	Disable Write Operations
RDSR	0000 0101	Read Status Register
WRSR	0000 0001	Write Status Register
READ	0000 0011	Read Data from Memory
WRITE	0000 0010	Write Data to Memory

Power-Up Timing⁽²⁾⁽³⁾

Symbol	Parameter	Max.	Units
t _{PUR}	Power-up to Read Operation	1	ms
tPUW	Power-up to Write Operation	1	ms

Note:

(1) X=0 for 25010, 25020. X=A8 for 25040

(2) This parameter is tested initially and after a design or process change that affects the parameter.

(3) t_{PUR} and t_{PUW} are the delays required from the time V_{CC} is stable until the specified operation can be initiated.



SCK: Serial Clock

SCK is the serial clock pin. This pin is used to synchro- WP is the Write Protect pin. The Write Protect pin will allow SCK. Data on the SO pin is updated on the falling edge of the SCK.

CS: Chip Select

CS is the Chip select pin. CS low enables the CAT25C33/ 65 and CS high disables the CAT25C33/65. CS high takes the SO output pin to high impedance and forces the devices into a Standby Mode (unless an internal write operation is underway). The CAT25C33/65 draws ZERO current in the Standby mode. A high to low transition on \overline{CS} is required prior to any sequence being initiated. A low to high transition on CS after a valid write sequence is what initiates an internal write cycle.

WP: Write Protect

nize the communication between the microcontroller normal read/write operations when held high. When \overline{WP} is and the 25C33/65. Opcodes, byte addresses, or data tied low and the WPEN bit in the status register is set to "1", present on the SI pin are latched on the rising edge of the all write operations to the status register are inhibited. WP going low while \overline{CS} is still low will interrupt a write to the status register. If the internal write cycle has already been initiated, WP going low will have no effect on any write operation to the status register. The \overline{WP} pin function is blocked when the WPEN bit is set to 0.

HOLD: Hold

The HOLD pin is used to pause transmission to the CAT25C33/65 while in the middle of a serial sequence without having to re-transmit entire sequence at a later time. To pause, HOLD must be brought low while SCK is low. The SO pin is in a high impedance state during the time the part is paused, and transitions on the SI pins will be ignored. To resume communication, HOLD is brought high, while SCK is low. (HOLD should be held high any time this function is not being used.) HOLD may be tied high

STATUS REGISTER

7	6	5	4	3	2	1	0
WPEN	X	Х	BP2	BP1	BP0	WEL	RDY

MEMORY PROTECTION

BP2	BP1	BP0	
0	0	0	Non-Protection
0	0	1	Q1 Protected
0	1	0	Q2 Protected
0	1	1	Q3 Protected
1	0	0	Q4 Protected
1	0	1	H1 Protected
1	1	0	P0 Protected
1	1	1	Pn Protected

MEMORY PROTECTION

CAT25C33	CAT25C65
0000-03FF	0000-07FF
0400-07FF	0800-0FFF
0800-0BFF	1000-17FF
0C00-0FFF	1800-1FFF
0000-07FF	0000-0FFF
0000-003F	0000-003F
0FC0-0FFF	0FC0-1FFF
	0000-03FF 0400-07FF 0800-0BFF 0C00-0FFF 0000-07FF 0000-003F

WRITE PROTECT ENABLE OPERATION

WPEN	WP	WEL	Protected Blocks	Unprotected Blocks	Status Register
0	Х	0	Protected	Protected	Protected
0	Х	1	Protected	Writable	Writable
1	Low	0	Protected	Protected	Protected
1	Low	1	Protected	Writable	Protected
Х	High	0	Protected	Protected	Protected
Х	High	1	Protected	Writable	Writable



directly to V_{cc} or tied to V_{cc} through a resistor. Figure 9 illustrates hold timing sequence.

STATUS REGISTER

The Status Register indicates the status of the device.

The RDY (Ready) bit indicates whether the CAT25C33/ 65 is busy with a write operation. When set to 1 a write cycle is in progress and when set to 0 the device indicates it is ready. This bit is read only.

The WEL (Write Enable) bit indicates the status of the write enable latch . When set to 1, the device is in a Write Enable state and when set to 0 the device is in a Write Disable state. The WEL bit can only be set by the WREN instruction and can be reset by the WRDI instruction.

The BP0, BP1 and BP2 (Block Protect) bits indicate which blocks are currently protected. These bits are set by the user issuing the WRSR instruction. The user is allowed to protect any quarter of the memory, the lower half of the memory, the first page or the last page by setting these bits. Once protected the user may only

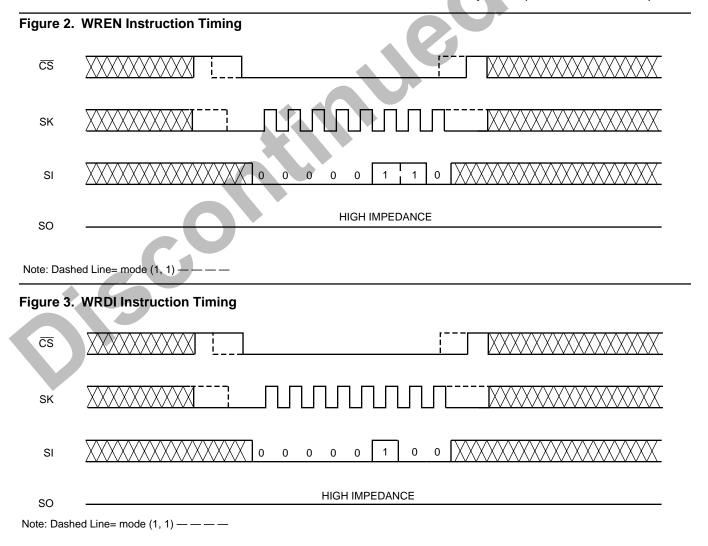
read from the protected portion of the array. These bits are non-volatile.

The WPEN (Write Protect Enable) is an enable bit for the \overline{WP} pin. The \overline{WP} pin and WPEN bit in the status register control the programmable hardware write protect feature. Hardware write protection is enabled when \overline{WP} is low and WPEN bit is set to high. The user cannot write to the status register (including the block protect bits and the WPEN bit) and the block protected sections in thememory array when the chip is hardware write protected. Only the sections of the memory array that are not block protected can be written. Hardware write protection is disabled when either \overline{WP} pin is high or the WPEN bit is zero.

DEVICE OPERATION

Write Enable and Disable

The CAT25C33/65 contains a write enable latch. This latch must be set before any write operation. The device powers





up in a write disable state when V_{cc} is applied. WREN instruction will enable writes (set the latch) to the device. WRDI instruction will disable writes (reset the latch) to the device. Disabling writes will protect the device against inadvertent writes.

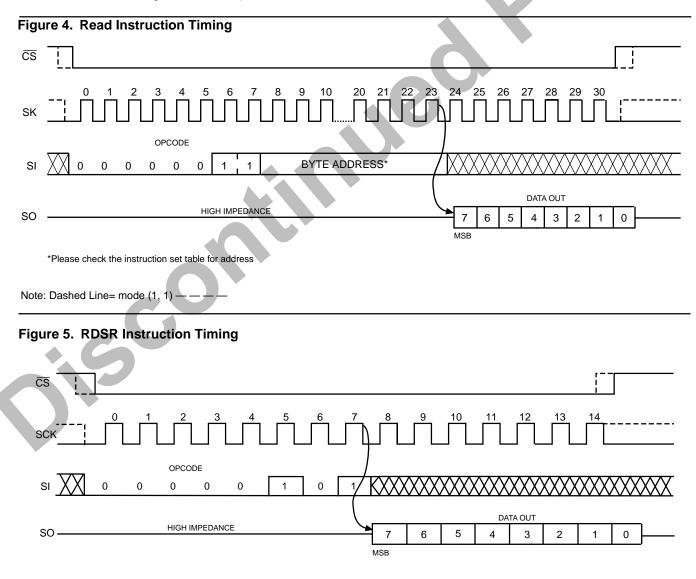
READ Sequence

The part is selected by pulling \overline{CS} low. The 8-bit read instruction is transmitted to the CAT25C33/65, followed by the 16-bit address (the three Most Significant Bits are don't care for 25C65 and four most significant bits are don't care for 25C33). After the correct read instruction and address are sent, the data stored in the memory at the selected address is shifted out on the SO pin. The data stored in the memory at the next address can be read sequentially by continuing to provide clock pulses. The internal address pointer is automatically incremented to the next higher address after each byte of data is shifted out. When the highest address (1FFFh for 25C65

and FFFh for 25C33) is reached, the address counter rolls over to 0000h allowing the read cycle to be continued indefinitely. The read operation is terminated by pulling the \overline{CS} high. To read the status register, RDSR instruction should be sent. The contents of the status register are shifted out on the SO line. The status register may be read at any time even during a write cycle. Read sequece is illustrated in Figure 4. Reading status register is illustrated in Figure 5.

WRITE Sequence

The CAT25C33/65 powers up in a Write Disable state. Prior to any write instructions, the WREN instruction must be sent to CAT25C33/65. The device goes into Write enable state by pulling the \overline{CS} low and then clocking the WREN instruction into CAT25C33/65. The \overline{CS} must be brought high after the WREN instruction to enable writes to the device.



Note: Dashed Line= mode (1, 1) - - - -



If the write operation is initiated immediately after the WREN instruction without \overline{CS} being brought high, the data will not be written to the array because the write enable latch will not have been properly set. Also, for a successful write operation the address of the memory location(s) to be programmed must be outside the protected address field location selected by the block protection level.

Byte Write

Once the device is in a Write Enable state, the user may proceed with a write sequence by setting the \overline{CS} low, issuing a write instruction via the SI line, followed by the 16-bit address (the three Most Significant Bits are don't care for 25C65 and four most significant bits are don't care for 25C33), and then the data to be written. Programming will start after the \overline{CS} is brought high. Figure 6 illustrates byte write sequence.

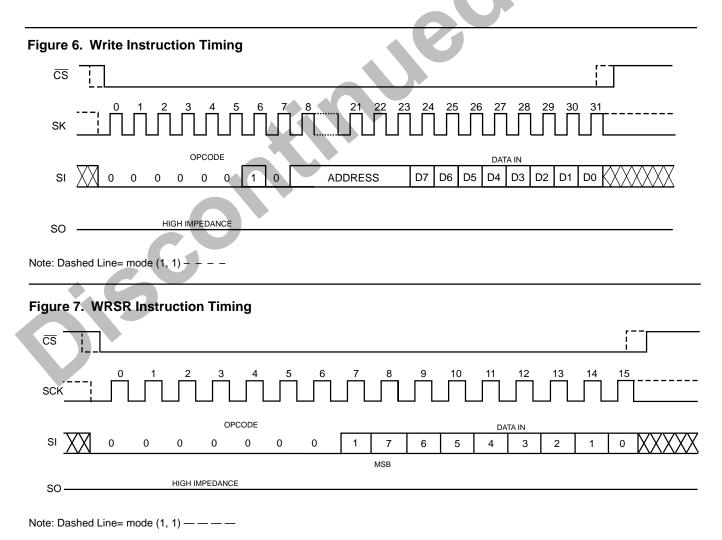
During an internal write cycle, all commands will be ignored except the RDSR (Read Status Register) instruction.

The Status Register can be read to determine if the write cycle is still in progress. If Bit 0 of the Status Register is set at 1, write cycle is in progress. If Bit 0 is set at 0, the device is ready for the next instruction.

Page Write

The CAT25C33/65 features page write capability. After the first initial byte the host may continue to write up to 64 bytes of data to the CAT25C33/65. After each byte of data is received, six lower order address bits are internally incremented by one; the high order bits of address will remain constant. The only restriction is that the 64 bytes must reside on the same page. If the address counter reaches the end of the page and clock continues, the counter will "roll over" to the first address of the page and overwrite any data that may have been written. The CAT25C33/65 is automatically returned to the write disable state at the completion of the write cycle. Figure 8 illustrates the page write sequence.

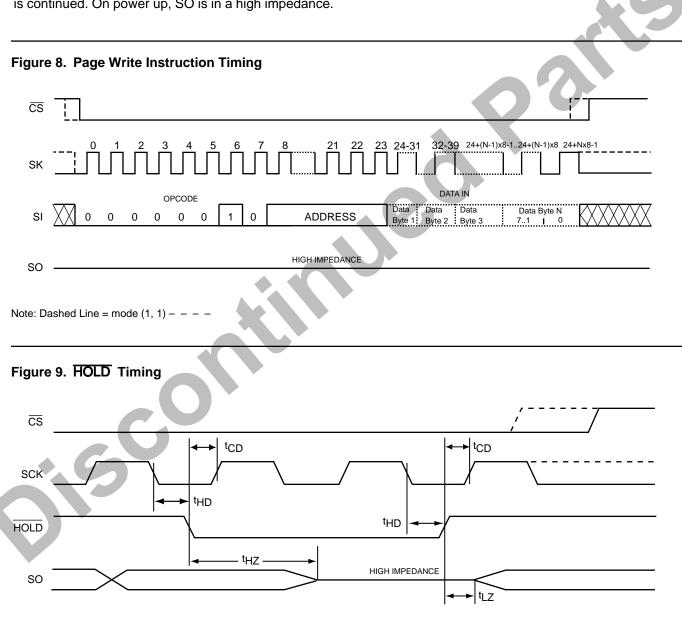
To write to the status register, the WRSR instruction should be sent. Only Bit 2, Bit 3 and Bit 7 of the status register can be written using the WRSR instruction. Figure 7 illustrates the sequence of writing to status register.





DESIGN CONSIDERATIONS

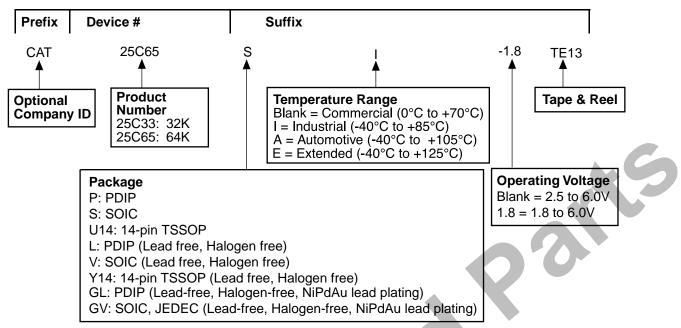
The CAT25C33/65 powers up in a write disable state and in a low power standby mode. A WREN instruction must be issued to perform any writes to the device after power up. Also,on power up CS should be brought low to enter a ready state and receive an instruction. After a successful byte/page write or status register write the CAT25C33/65 goes into a write disable mode. CS must be set high after the proper number of clock cycles to start an internal write cycle. Access to the array during an internal write cycle is ignored and program-ming is continued. On power up, SO is in a high impedance. When powering down, the supply should be taken down to 0V, so that the CAT25C33/65 will be reset when power is ramped back up. If this is not possible, then, following a brown-out episode, the CAT25C33/65 can be reset by refreshing the contents of the Status Register (See Application Note AN10).



Note: Dashed Line= mode (1, 1) - - -



ORDERING INFORMATION



Notes:

(1) The device used in the above example is a 25C65SI-1.8TE13 (SOIC, Industrial Temperature, 1.8 Volt to 6 Volt Operating Voltage, Tape & Reel)

SCO

REVISION HISTORY

Date	Rev.	Reason	
8/5/2004	F	Updated Features	
		Updated DC Operating Characteristics table & notes	
07/11/2005	G	Update Reliability Characteristic	
		Update Ordering Information	
09/22/2005	Н	Update Pin Configuration	

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